

SOT-23



Pin Definition:

1. Gate
2. Source
3. Drain

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
-30	180 @ $V_{GS} = -10V$	-1.3
	300 @ $V_{GS} = -4.5V$	-1.1

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

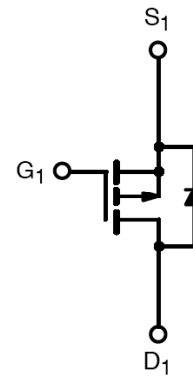
- Portable Devices
- High Speed Switch

Ordering Information

Part No.	Package	Packing
TSM2303CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-1.3	A
Pulsed Drain Current	I_{DM}	-10	A
Continuous Source Current (Diode Conduction) ^{a,b}	I_S	-1.3	A
Maximum Power Dissipation	P_D	0.7	W
		0.45	
Operating Junction Temperature	T_J	+150	$^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R_{\theta JC}$	80	$^\circ C/W$
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\theta JA}$	140	$^\circ C/W$

Notes:

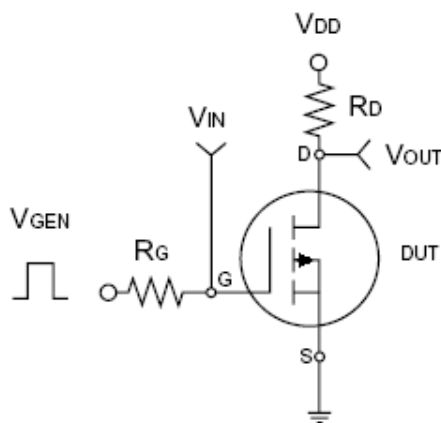
- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on a 1 in² pad of 2oz Cu, $t \leq 5$ sec.

Electrical Specifications (Ta = 25°C unless otherwise noted)

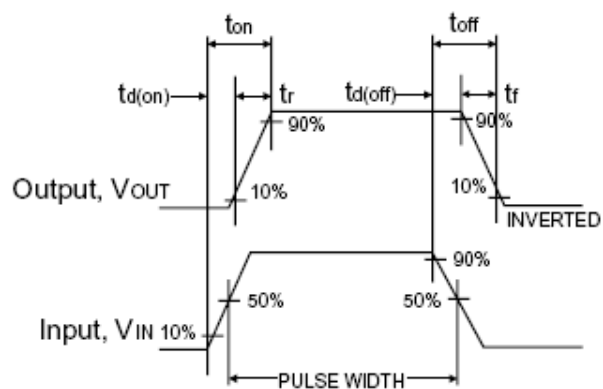
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	-30	--	--	V
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	V _{GS(TH)}	-1	--	-3	V
Gate Body Leakage	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V	I _{DSS}	--	--	1.0	μA
Drain-Source On-State Resistance	V _{GS} = -10V, I _D = -1.3A	R _{DS(ON)}	--	150	180	mΩ
	V _{GS} = -4.5V, I _D = -1.1A		--	250	300	
Forward Transconductance ^a	V _{DS} = -15V, I _D = -1.3A	g _{fs}	--	5	--	S
Diode Forward Voltage	I _S = -1.3A, V _{GS} = 0V	V _{SD}	--	--	-1.2	V
Dynamic ^b						
Total Gate Charge	V _{DS} = -10V, I _D = -1.3A, V _{GS} = -4.5V	Q _g	--	10	15	nC
Gate-Source Charge		Q _{gs}	--	1.9	--	
Gate-Drain Charge		Q _{gd}	--	2	--	
Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	565	--	pF
Output Capacitance		C _{oss}	--	126	--	
Reverse Transfer Capacitance		C _{rss}	--	75	--	
Switching ^{b,c}						
Turn-On Delay Time	V _{DD} = -10V, R _L = 15Ω, I _D = -1A, V _{GEN} = -4.5V, R _G = 6Ω	t _{d(on)}	--	10	--	nS
Turn-On Rise Time		t _r	--	9	--	
Turn-Off Delay Time		t _{d(off)}	--	27	--	
Turn-Off Fall Time		t _f	--	7	--	

Notes:

- a. pulse test: PW ≤ 300μS, duty cycle ≤ 2%
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature.



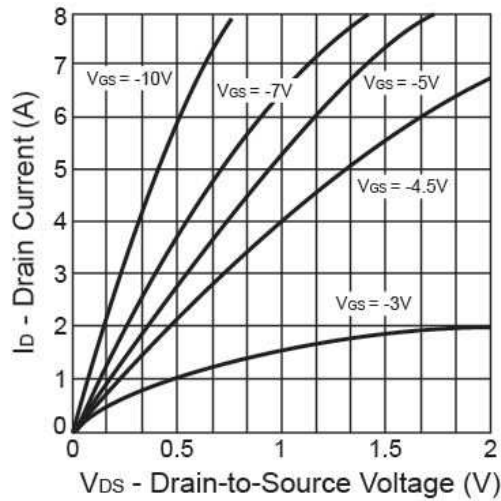
Switching Test Circuit



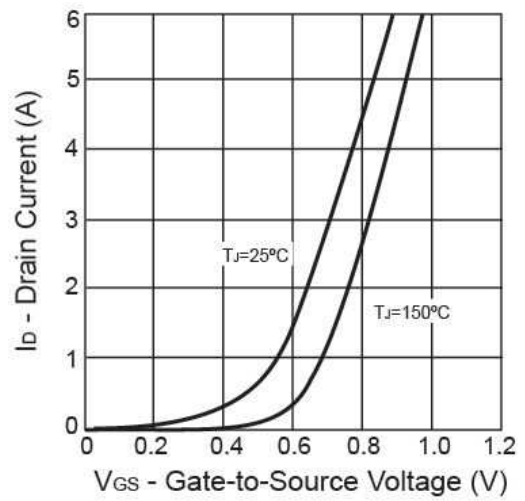
Switchin Waveforms

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

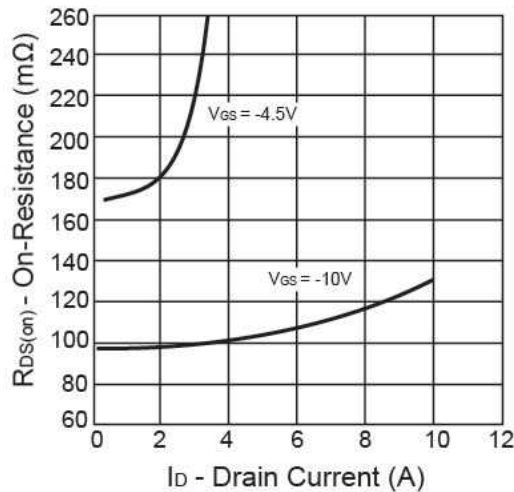
Output Characteristics



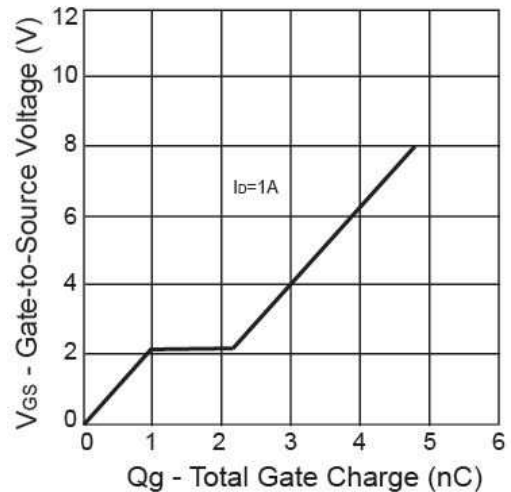
Transfer Characteristics



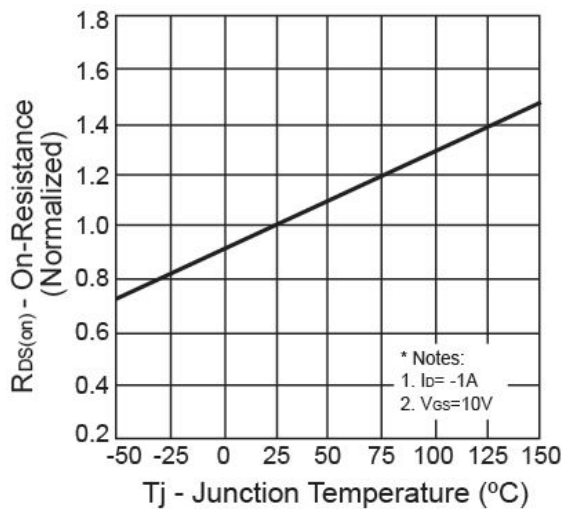
On-Resistance vs. Drain Current



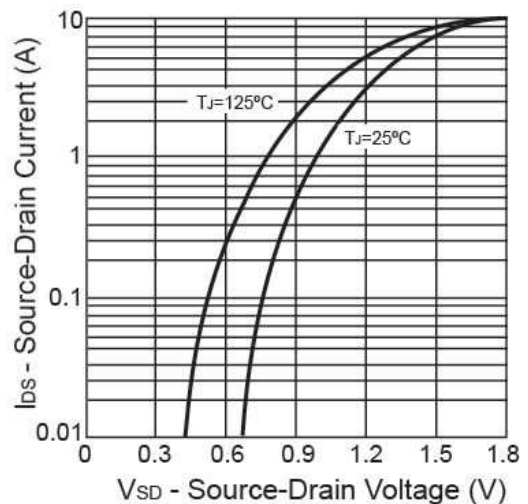
Gate Charge



On-Resistance vs. Junction Temperature

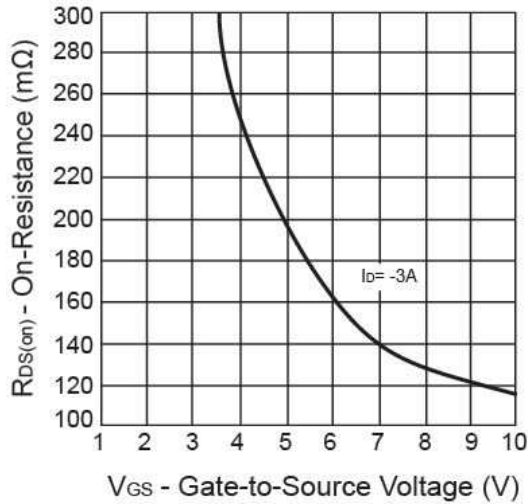


Source-Drain Diode Forward Voltage

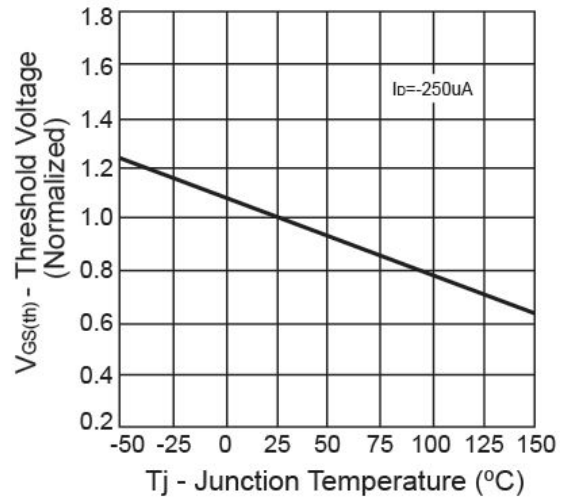


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

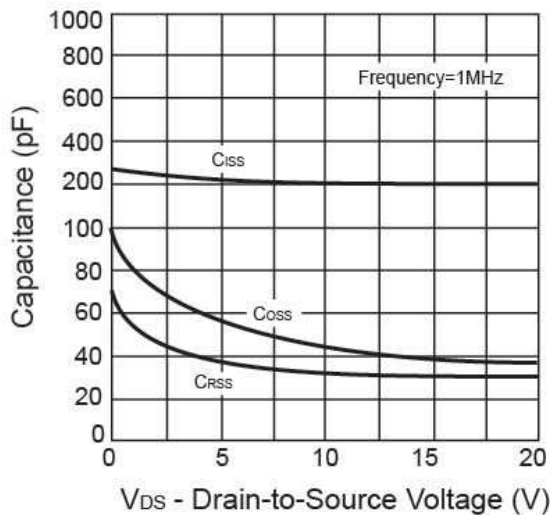
On-Resistance vs. Gate-Source Voltage



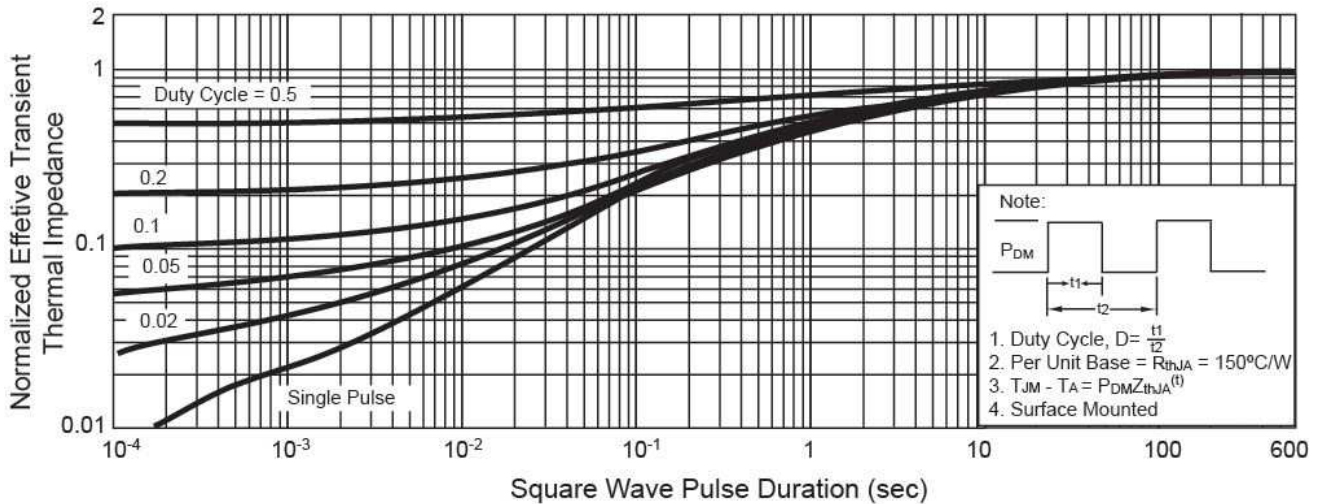
Threshold Voltage



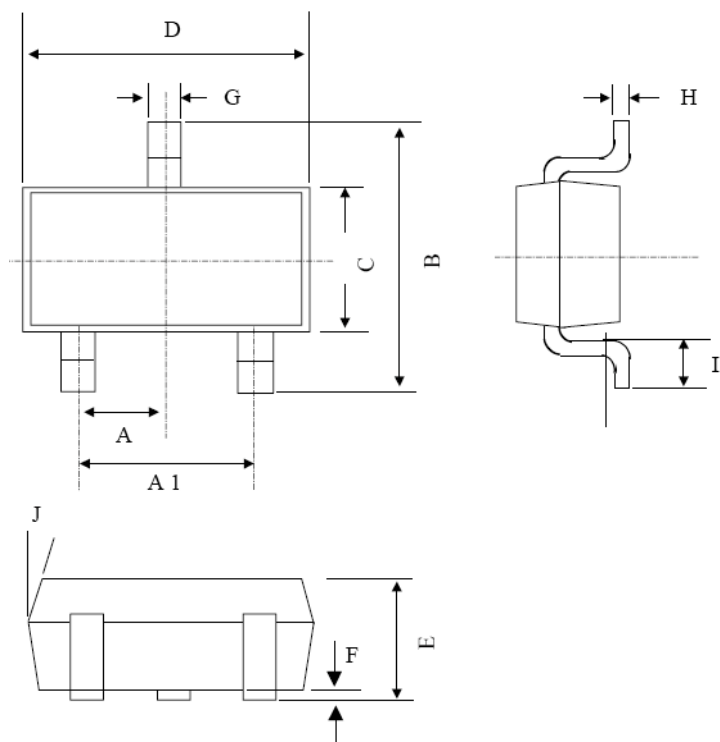
Capacitance



Normalized Thermal Transient Impedance, Junction-to-Ambient

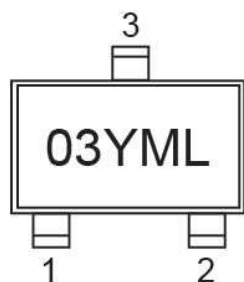


SOT-23 Mechanical Drawing



SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	0.95 BSC		0.037 BSC	
A1	1.9 BSC		0.074 BSC	
B	2.60	3.00	0.102	0.118
C	1.40	1.70	0.055	0.067
D	2.80	3.10	0.110	0.122
E	1.00	1.30	0.039	0.051
F	0.00	0.10	0.000	0.004
G	0.35	0.50	0.014	0.020
H	0.10	0.20	0.004	0.008
I	0.30	0.60	0.012	0.024
J	5°	10°	5°	10°

Marking Diagram



03 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code

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